

Shinji Migita

List of Publications by Year in descending order

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times ranked

2146
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Evolution of ferroelectric HfO ₂ in ultrathin region down to 3â€%nm. Applied Physics Letters, 2018, 112, . | 3.3 | 188 |
| 2 | Kinetic pathway of the ferroelectric phase formation in doped HfO ₂ films. Journal of Applied Physics, 2017, 122, . | 2.5 | 150 |
| 3 | Experimental evidence for the flatband voltage shift of high-k metal-oxide-semiconductor devices due to the dipole formation at the high-kâ•SiO ₂ interface. Applied Physics Letters, 2008, 92, . | 3.3 | 140 |
| 4 | Ferroelectric phase stabilization of HfO ₂ by nitrogen doping. Applied Physics Express, 2016, 9, 091501. | 2.4 | 84 |
| 5 | Polarization switching behavior of Hfâ€Zrâ€O ferroelectric ultrathin films studied through coercive field characteristics. Japanese Journal of Applied Physics, 2018, 57, 04FB01. | 1.5 | 79 |
| 6 | Fully coupled 3-D device simulation of negative capacitance FinFETs for sub 10 nm integration. , 2016, , . | | 77 |
| 7 | Ferroelectricity of nondoped thin HfO ₂ films in TiN/HfO ₂ /TiN stacks. Japanese Journal of Applied Physics, 2016, 55, 08PB01. | 1.5 | 68 |
| 8 | Experimental Demonstration of Ultrashort-Channel (3 nm) Junctionless FETs Utilizing Atomically Sharp V-Grooves on SOI. IEEE Nanotechnology Magazine, 2014, 13, 208-215. | 2.0 | 59 |
| 9 | Study of tunneling transport in Si-based tunnel field-effect transistors with ON current enhancement utilizing isoelectronic trap. Applied Physics Letters, 2015, 106, . | 3.3 | 54 |
| 10 | Performance Enhancement of Tunnel Field-Effect Transistors by Synthetic Electric Field Effect. IEEE Electron Device Letters, 2014, 35, 792-794. | 3.9 | 53 |
| 11 | Thermodynamic control of ferroelectric-phase formation in Hf _x Zr _{1-x} O ₂ and ZrO ₂ . Journal of Applied Physics, 2018, 124, . | 2.5 | 48 |
| 12 | Comprehensive Study of V</inf>FB</inf> Shift in High-k CMOS - Dipole Formation, Fermi-level Pinning and Oxygen Vacancy Effect. , 2007, , . | | 39 |
| 13 | Phase transformation behavior of ultrathin Hf _{0.5} Zr _{0.5} O ₂ films investigated through wide range annealing experiments. Japanese Journal of Applied Physics, 2019, 58, SBBA07. | 1.5 | 38 |
| 14 | Self-limiting process for the bismuth content in molecular beam epitaxial growth of Bi ₂ Sr ₂ CuO _y thin films. Applied Physics Letters, 1997, 71, 3712-3714. | 3.3 | 36 |
| 15 | Unexpected equivalent-oxide-thickness dependence of the subthreshold swing in tunnel field-effect transistors. Applied Physics Express, 2014, 7, 024201. | 2.4 | 35 |
| 16 | Decomposition of On-Current Variability of nMOS FinFETs for Prediction Beyond 20 nm. IEEE Transactions on Electron Devices, 2012, 59, 2003-2010. | 3.0 | 27 |
| 17 | Electrical performances of junctionless-FETs at the scaling limit (L</inf>CH</inf>) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tt 25 | | 25 |
| 18 | A compact model for tunnel field-effect transistors incorporating nonlocal band-to-band tunneling. Journal of Applied Physics, 2013, 114, 144512. | 2.5 | 25 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Epitaxial Bi ₄ Ti ₃ O ₁₂ thin film growth using Bi self-limiting function. Journal of Crystal Growth, 1999, 200, 161-168. | 1.5 | 24 |
| 20 | Re-examination of Flat-Band Voltage Shift for High-k MOS Devices. , 2007, , . | | 22 |
| 21 | Intrinsic Origin of Electron Mobility Reduction in High-k MOSFETs - From Remote Phonon to Bottom Interface Dipole Scattering. , 2007, , . | | 22 |
| 22 | Suppressing V_{th} and G_m variability of FinFETs using amorphous metal gates for 14 nm and beyond. , 2012, , . | | 22 |
| 23 | Band-to-band tunneling current enhancement utilizing isoelectronic trap and its application to TFETs. , 2014, , . | | 22 |
| 24 | Epitaxial structure SrTiO ₃ on Si. Journal of Applied Physics, 2001, 89, 5421-5424. | 2.5 | 21 |
| 25 | Symmetrical threshold voltage in complementary metal-oxide-semiconductor field-effect transistors with HfAlO _x (N) achieved by adjusting Hf/Al compositional ratio. Journal of Applied Physics, 2006, 99, 054506. | 2.5 | 21 |
| 26 | Fabrication and Demonstration of 3-nm-Channel-Length Junctionless Field-Effect Transistors on Silicon-on-Insulator Substrates Using Anisotropic Wet Etching and Lateral Diffusion of Dopants. Japanese Journal of Applied Physics, 2013, 52, 04CA01. | 1.5 | 21 |
| 27 | Design and demonstration of very high-k ($k_{eff} \approx 50$) HfO ₂ for ultra-scaled Si CMOS. , 2008, , . | | 20 |
| 28 | Physical origins of mobility enhancement of Ge p-channel metal-insulator-semiconductor field effect transistors with Si passivation layers. Journal of Applied Physics, 2010, 108, 104511. | 2.5 | 20 |
| 29 | Material and device engineering in fully depleted silicon-on-insulator transistors to realize a steep subthreshold swing using negative capacitance. Japanese Journal of Applied Physics, 2016, 55, 08PD01. | 1.5 | 20 |
| 30 | Nanometer-scale crystallization of thin HfO ₂ films studied by HF-chemical etching. Applied Physics Letters, 2005, 86, 212907. | 3.3 | 18 |
| 31 | Achievement of Higher-k and High- ϵ_{eff} in Phase Controlled HfO ₂ Film Using Post Gate Electrode Deposition Annealing. ECS Transactions, 2007, 11, 35-45. | 0.5 | 18 |
| 32 | (111)-Faceted Metal Source and Drain for Aggressively Scaled Metal/High-k MISFETs. IEEE Transactions on Electron Devices, 2008, 55, 1244-1249. | 3.0 | 18 |
| 33 | Nature of interface traps in Ge metal-insulator-semiconductor structures with GeO ₂ interfacial layers. Journal of Applied Physics, 2011, 109, . | 2.5 | 18 |
| 34 | Experimental realization of complementary p- and n- tunnel FinFETs with subthreshold slopes of less than 60 mV/decade and very low ($I_{off} < 10^{-3}$ mA) off-current on a Si CMOS platform. , 2014, , . | | 18 |
| 35 | Perspective of negative capacitance FinFETs investigated by transient TCAD simulation. , 2017, , . | | 17 |
| 36 | Impact of Surface Hydrophilicization prior to Atomic Layer Deposition for HfO ₂ /Si Direct-Contact Gate Stacks. Applied Physics Express, 2009, 2, 011201. | 2.4 | 16 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | Tunnel Field-Effect Transistor with Epitaxially Grown Tunnel Junction Fabricated by Source/Drain-First and Tunnel-Junction-Last Processes. Japanese Journal of Applied Physics, 2013, 52, 04CC25. | 1.5 | 16 |
| 38 | Fringing field effects in negative capacitance field-effect transistors with a ferroelectric gate insulator. Japanese Journal of Applied Physics, 2018, 57, 04FD07. | 1.5 | 16 |
| 39 | Partial silicides technology for tunable work function electrodes on high-k gate dielectrics - fermi level pinning controlled PtS/sub X/, for HfO/sub X/(N) pMOSFET. , 0, , . | | 15 |
| 40 | Suppression of threshold voltage variability of double-gate fin field-effect transistors using amorphous metal gate with uniform work function. Applied Physics Letters, 2013, 102, . | 3.3 | 15 |
| 41 | Introduction of SiGe/Si heterojunction into novel multilayer tunnel FinFET. Japanese Journal of Applied Physics, 2016, 55, 04EB06. | 1.5 | 15 |
| 42 | Tunnel FinFET CMOS inverter with very low short-circuit current for ultralow-power Internet of Things application. Japanese Journal of Applied Physics, 2017, 56, 04CD19. | 1.5 | 15 |
| 43 | Accelerated ferroelectric phase transformation in HfO ₂ /ZrO ₂ nanolaminates. Applied Physics Express, 2021, 14, 051006. | 2.4 | 15 |
| 44 | Particle-free superconducting Bi ₂ Sr ₂ CaCu ₂ O _x ultrathin films prepared by atomic-layer-controlled molecular beam epitaxy technique. Physica C: Superconductivity and Its Applications, 1999, 311, 42-48. | 1.2 | 14 |
| 45 | Memory properties of a ferroelectric gate field-effect transistor with an adjoining metal-ferroelectric-metal assistance cell. Journal of Applied Physics, 2003, 94, 2559-2562. | 2.5 | 14 |
| 46 | Accurate evaluation of Ge metal-insulator-semiconductor interface properties. Journal of Applied Physics, 2011, 110, . | 2.5 | 14 |
| 47 | Fabrication of Direct-Contact Higher-k HfO ₂ Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01. | 1.5 | 14 |
| 48 | Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653. | 3.0 | 14 |
| 49 | General relationship for cation and anion doping effects on ferroelectric HfO ₂ formation. , 2016, , . | | 14 |
| 50 | Molecular beam epitaxial growth of SrO and CaO with RHEED intensity oscillation. Journal of Low Temperature Physics, 1996, 105, 1337-1342. | 1.4 | 13 |
| 51 | All-perovskite-oxide ferroelectric memory transistor composed of Bi ₂ Sr ₂ CuO _x and PbZr _{0.5} Ti _{0.5} O ₃ films. Journal of Applied Physics, 2001, 89, 8153-8158. | 2.5 | 13 |
| 52 | Pulsed laser deposition and ferroelectric properties of SrBi ₂ Ta ₂ O ₉ thin films. Materials Letters, 1999, 38, 406-412. | 2.6 | 12 |
| 53 | Influence of work function variation of metal gates on fluctuation of sub-threshold drain current for fin field-effect transistors with undoped channels. Japanese Journal of Applied Physics, 2014, 53, 04EC11. | 1.5 | 12 |
| 54 | Two-step annealing effects on ultrathin EOT higher-k (k=40) ALD-HfO ₂ gate stacks. Solid-State Electronics, 2013, 84, 58-64. | 1.4 | 11 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 55 | The influence of Bi-sticking coefficient in the growth of Bi(2212) thin film by ion beam sputtering. Thin Solid Films, 1996, 281-282, 510-512. | 1.8 | 10 |
| 56 | Surface Morphology and Dielectric Properties of Stoichiometric and Off-Stoichiometric SrTiO ₃ Thin Films Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1535-L1537. | 1.5 | 10 |
| 57 | Growth Style of Bi ₄ Ti ₃ O ₁₂ Thin Films on CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ Buffered Si Substrates. Japanese Journal of Applied Physics, 1999, 38, 5411-5416. | 1.5 | 10 |
| 58 | Fabrication and critical currents of thin-film-type Bi ₂ Sr ₂ CaCu ₂ O _x intrinsic Josephson junctions. Physica C: Superconductivity and Its Applications, 2001, 362, 256-260. | 1.2 | 10 |
| 59 | Enhancement of the ultraviolet absorption and Raman efficiencies of a few nanometer thick Si-on-insulator. Journal of Applied Physics, 2012, 112, 074317. | 2.5 | 10 |
| 60 | Accurate prediction of PBTI lifetime for N-type fin-channel tunnel FETs. , 2014, , . | | 10 |
| 61 | Magnetic anomaly of Y _{1-x} Sr _x VO ₃ . Physica C: Superconductivity and Its Applications, 1999, 317-318, 464-470. | 1.2 | 9 |
| 62 | Predictivity of the non-local BTBT model for structure dependencies of tunnel FETs. , 2014, , . | | 9 |
| 63 | Lowest variability SOI FinFETs having multiple V _t by back-biasing. , 2014, , . | | 9 |
| 64 | Effect of hot implantation on ON-current enhancement utilizing isoelectronic trap in Si-based tunnel field-effect transistors. Applied Physics Express, 2015, 8, 036503. | 2.4 | 9 |
| 65 | Demonstrating performance improvement of complementary TFET circuits by I _{on} enhancement based on isoelectronic trap technology. , 2016, , . | | 9 |
| 66 | Structural advantages of silicon-on-insulator FETs over FinFETs in steep subthreshold-swing operation in ferroelectric-gate FETs. Japanese Journal of Applied Physics, 2017, 56, 04CD10. | 1.5 | 9 |
| 67 | Multidomain Dynamics of Ferroelectric Polarization and its Coherency-Breaking in Negative Capacitance Field-Effect Transistors. , 2018, , . | | 9 |
| 68 | Regulating phase transformation kinetics via redox reaction in ferroelectric Ge-doped HfO ₂ . Applied Physics Letters, 2020, 117, . | 3.3 | 9 |
| 69 | Gate-First Processed FUSI/HfO ₂ /HfSiO _x /Si MOSFETs with EOT=0.5 nm - Interfacial Layer Formation by Cycle-by-Cycle Deposition and Annealing. , 2007, , . | | 8 |
| 70 | Impact of reduced pressure crystallization on ferroelectric properties in hafnium-zirconium dioxide films deposited by sputtering. Japanese Journal of Applied Physics, 2021, 60, SFFB05. | 1.5 | 8 |
| 71 | Structural Metastability and Size Scalability of Phase-Controlled HfO ₂ Formed through Cap-PDA. ECS Transactions, 2009, 19, 563-575. | 0.5 | 7 |
| 72 | Performance evaluation of parallel electric field tunnel field-effect transistor by a distributed-element circuit model. Solid-State Electronics, 2014, 102, 82-86. | 1.4 | 7 |

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| 73 | Impact of granular work function variation in a gate electrode on low-frequency noise for fin field-effect transistors. Applied Physics Express, 2015, 8, 044201. | 2.4 | 7 |
| 74 | Ultra-short channel junctionless transistor with a one-dimensional nanodot array floating gate. Applied Physics Letters, 2015, 106, . | 3.3 | 7 |
| 75 | Extremely Scaled ($\sim 1/40.2$ nm) Equivalent Oxide Thickness of Higher-k ($k=40$) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04. | 1.5 | 7 |
| 76 | Comparison between Bi-superconductor thin films fabricated via co-deposition and layer-by-layer deposition by ion beam sputtering method. Thin Solid Films, 1996, 281-282, 517-520. | 1.8 | 6 |
| 77 | Epitaxial Growth of Bi ₄ Ti ₃ O ₁₂ /CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ and Bi ₄ Ti ₃ O ₁₂ /SrTiO ₃ /Ce _{0.12} Zr _{0.88} O ₂ Thin Films on Si and Its Application to Metal-Ferroelectric-Insulator-Semiconductor Diodes. Japanese Journal of Applied Physics, 2000, 39, 5505-5511. | 1.5 | 6 |
| 78 | Silicon-Atom Induced Fermi-Level Pinning of Fully Silicided Platinum Gates on HfO ₂ Dielectrics. Japanese Journal of Applied Physics, 2005, 44, 2267-2272. | 1.5 | 6 |
| 79 | Study on Oxynitride Buffer Layers in HfO ₂ Metal-Insulator-Semiconductor Structures for Improving Metal-Insulator-Semiconductor Field-Effect Transistor Performance. Japanese Journal of Applied Physics, 2005, 44, 1698-1703. | 1.5 | 6 |
| 80 | AFM measurement of atomic-scale Si surface etching by active oxidation. Surface Science, 2010, 604, 1432-1437. | 1.9 | 6 |
| 81 | First demonstration of drain current enhancement in SOI tunnel FET with vertical-tunnel-multiplication. , 2012, , . | | 6 |
| 82 | Improvement of epitaxial channel quality on heavily arsenic- and boron-doped Si surfaces and impact on performance of tunnel field-effect transistors. Solid-State Electronics, 2015, 113, 173-178. | 1.4 | 6 |
| 83 | Study of wake-up and fatigue properties in doped and undoped ferroelectric HfO ₂ in conjunction with piezo-response force microscopy analysis. , 2016, , . | | 6 |
| 84 | Thickness-independent behavior of coercive field in HfO ₂ -based ferroelectrics. , 2017, , . | | 6 |
| 85 | (Invited) Relationship between Ferroelectricity and Electrical Breakdown in Hf-Zr-O Thin Films. ECS Transactions, 2017, 80, 247-252. | 0.5 | 6 |
| 86 | Design points of ferroelectric field-effect transistors for memory and logic applications as investigated by metal-ferroelectric-metal-insulator-semiconductor gate stack structures using Hf _{0.5} Zr _{0.5} O ₂ films. Japanese Journal of Applied Physics, 2019, 58, SLLB06. | 1.5 | 6 |
| 87 | Thermal stability of ferroelectricity in hafnium-zirconium dioxide films deposited by sputtering and chemical solution deposition for oxide-channel ferroelectric-gate transistor applications. Applied Physics Express, 2021, 14, 041006. | 2.4 | 6 |
| 88 | Investigation of the wake-up process and time-dependent imprint of Hf _{0.5} Zr _{0.5} O ₂ film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, . | 3.3 | 6 |
| 89 | Epitaxial structure SrBi ₂ Ta ₂ O ₉ / SrTiO ₃ / Ce _{0.12} Zr _{0.88} O ₂ / Si for ferroelectric-gate FET memory. Integrated Ferroelectrics, 2001, 40, 135-143. | 0.7 | 5 |
| 90 | Heated ion implantation technology for highly reliable metal-gate/high-k CMOS SOI FinFETs. , 2013, , . | | 5 |

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| 91 | Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. Journal of Low Power Electronics and Applications, 2014, 4, 153-167. | 2.0 | 5 |
| 92 | Robust and compact key generator using physically unclonable function based on logic-transistor-compatible poly-crystalline-Si channel FinFET technology. , 2015, , . | | 5 |
| 93 | Suppression of tunneling rate fluctuations in tunnel field-effect transistors by enhancing tunneling probability. Japanese Journal of Applied Physics, 2017, 56, 04CD02. | 1.5 | 5 |
| 94 | Fabrication of Direct-Contact Higher- k HfO ₂ Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01. | 1.5 | 5 |
| 95 | Nanometer level etching and deposition of Bi-Sr-Ca-Cu-O superconducting thin films. , 1996, , . | | 4 |
| 96 | Extremely Scaled (~ 0.2 nm) Equivalent Oxide Thickness of Higher- k ($k = 40$) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04. | 1.5 | 4 |
| 97 | Performance limit of parallel electric field tunnel FET and improvement by modified gate and channel configurations. , 2013, , . | | 4 |
| 98 | Scaling breakthrough for analog/digital circuits by suppressing variability and low-frequency noise for FinFETs by amorphous metal gate technology. , 2014, , . | | 4 |
| 99 | Variation behavior of tunnel-FETs originated from dopant concentration at source region and channel edge configuration. , 2014, , . | | 4 |
| 100 | Importance of interface engineering for synthesis of SrHfO ₃ perovskite thin films on Si substrates through crystallization of amorphous films and control of flat-band voltages of metal-oxide-semiconductor capacitors. Japanese Journal of Applied Physics, 2014, 53, 04EA03. | 1.5 | 4 |
| 101 | (Invited) Charge Trapping Type SOI-FinFET Flash Memory. ECS Transactions, 2014, 61, 263-280. | 0.5 | 4 |
| 102 | Heated ion implantation for high-performance and highly reliable silicon-on-insulator complementary metal-oxide-silicon fin field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DA06. | 1.5 | 4 |
| 103 | Epitaxial growth of Ge thin film on Si (001) by DC magnetron sputtering. Materials Science in Semiconductor Processing, 2017, 70, 3-7. | 4.0 | 4 |
| 104 | Lateral variations of the surface electric potential and elastic stiffness of ultrathin Hf _{0.5} Zr _{0.5} O ₂ films on silicon. AIP Advances, 2021, 11, 015216. | 1.3 | 4 |
| 105 | Effect of Ge Metal-Insulator-Semiconductor Interfacial Layers on Interface Trap Density near the Conduction Band Edge. Japanese Journal of Applied Physics, 2010, 49, 04DA09. | 1.5 | 3 |
| 106 | (Invited) Epitaxial HfO ₂ Thin Films on Si Substrates: Strategy for Sub-1 nm EOT Technology. ECS Transactions, 2011, 41, 135-144. | 0.5 | 3 |
| 107 | Analysis of threshold voltage shifts in double gate tunnel FinFETs: Effects of improved electrostatics by gate dielectrics and back gate effects. , 2013, , . | | 3 |
| 108 | Impact of fin length on threshold voltage modulation by back bias for Independent double-gate tunnel fin field-effect transistors. Solid-State Electronics, 2015, 111, 62-66. | 1.4 | 3 |

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| 109 | Impact of extension implantation conditions of fin field-effect transistors on gate-induced drain leakage. Japanese Journal of Applied Physics, 2016, 55, 04EB01. | 1.5 | 3 |
| 110 | Impact of residual defects caused by extension ion implantation in FinFETs on parasitic resistance and its fluctuation. Solid-State Electronics, 2017, 132, 103-108. | 1.4 | 3 |
| 111 | Simulation study of short-channel effects of tunnel field-effect transistors. Japanese Journal of Applied Physics, 2018, 57, 04FD04. | 1.5 | 3 |
| 112 | Device Simulation of Negative-Capacitance Field-Effect Transistors With a Ferroelectric Gate Insulator. , 2018, , . | | 3 |
| 113 | Growth mechanism of epitaxial NiSi ₂ in atomic-scale for Schottky source/drain in Silicon Nanowire transistors. , 2009, , . | | 2 |
| 114 | Cryogenic operation of double-gate FinFET and demonstration of analog circuit at 4.2K. , 2012, , . | | 2 |
| 115 | TDDB characteristics of thin polycrystalline and amorphous HfO ₂ films. , 2014, , . | | 2 |
| 116 | Experimental study of three-dimensional fin-channel charge trapping flash memories with titanium nitride and polycrystalline silicon gates. Japanese Journal of Applied Physics, 2014, 53, 04ED16. | 1.5 | 2 |
| 117 | Fluctuation in drain induced barrier lowering (DIBL) for FinFETs caused by granular work function variation of metal gates. , 2014, , . | | 2 |
| 118 | Understanding of BTI for tunnel FETs. , 2015, , . | | 2 |
| 119 | Steep subthreshold swing and energy efficiency in MOSFETs utilizing nonlinear gate dielectric insulators. Japanese Journal of Applied Physics, 2016, 55, 04ED02. | 1.5 | 2 |
| 120 | On the drain bias dependence of long-channel silicon-on-insulator-based tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CD04. | 1.5 | 2 |
| 121 | Bias temperature instability in tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CA04. | 1.5 | 2 |
| 122 | Design of steep-slope negative-capacitance FinFETs for dense integration: Importance of appropriate ferroelectric capacitance and short-channel effects. Japanese Journal of Applied Physics, 2018, 57, 04FD03. | 1.5 | 2 |
| 123 | Assessment of Steep-Subthreshold Swing Behaviors in Ferroelectric-Gate Field-Effect Transistors Caused by Positive Feedback of Polarization Reversal. , 2018, , . | | 2 |
| 124 | One-dimensional array of gold nanoparticles fabricated using biotemplate and its application to fine FET. Japanese Journal of Applied Physics, 2018, 57, 06HC05. | 1.5 | 2 |
| 125 | Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. Japanese Journal of Applied Physics, 2015, 54, 04DD04. | 1.5 | 2 |
| 126 | Enhancement of ferroelectricity in sputtered HZO thin films by catalytically generated atomic hydrogen treatment. Japanese Journal of Applied Physics, 2022, 61, SH1004. | 1.5 | 2 |

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| 127 | Evaluation of Ozone Condensation System by Thermal Decomposition Method. Japanese Journal of Applied Physics, 1997, 36, 94-97. | 1.5 | 1 |
| 128 | Fabrication and Electrical Characteristics of a Trench-Type Metal-Ferroelectric-Metal-Insulator-Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2001, 40, 5605-5609. | 1.5 | 1 |
| 129 | Exact control of junction position using epitaxial NiSi ₂ crystallization in ultrathin silicon-on-insulator metal-oxide-semiconductor field-effect transistors. AIP Advances, 2012, 2, . | 1.3 | 1 |
| 130 | Impact of atomic-scale structural design on ultra-short channel (3 nm) MOSFETs. , 2013, , . | | 1 |
| 131 | Variability of short channel junctionless field-effect transistors caused by fluctuation of dopant concentration. , 2013, , . | | 1 |
| 132 | Guidelines for symmetric threshold voltage in tunnel FinFETs with single and dual metal gate electrodes. , 2013, , . | | 1 |
| 133 | Fabrication and characterization of 3D fin-channel MANOS type flash memory. , 2014, , . | | 1 |
| 134 | Study of gate leakage current paths in p-channel tunnel field-effect transistor by current separation measurement and device simulation. Japanese Journal of Applied Physics, 2015, 54, 034202. | 1.5 | 1 |
| 135 | PBTI for N-type tunnel FinFETs. , 2015, , . | | 1 |
| 136 | Design and simulation of steep-slope silicon-on-insulator FETs using negative capacitance: Impact of buried oxide thickness and remnant polarization. , 2016, , . | | 1 |
| 137 | Charge effects of ultrafine FET with nanodot type floating gate. , 2016, , . | | 1 |
| 138 | (Invited) Floating Gate Type SOI-FinFET Flash Memories with Different Channel Shapes and Interpoly Dielectric Materials. ECS Transactions, 2016, 72, 11-24. | 0.5 | 1 |
| 139 | Device simulation of negative-capacitance field-effect transistors with a uniaxial ferroelectric gate insulator. Nonlinear Theory and Its Applications IEICE, 2020, 11, 145-156. | 0.6 | 1 |
| 140 | Impact of annealing on electric and elastic properties of 10-nm Hf _{0.5} Zr _{0.5} O ₂ films prepared on Si by sputtering. Microelectronic Engineering, 2022, 258, 111770. | 2.4 | 1 |
| 141 | Superconductivity and magnetic transitions of La ₂ â ^x CuO _y system under 60kbar O ₂ -HIP treatment. Physica C: Superconductivity and Its Applications, 1991, 185-189, 775-776. | 1.2 | 0 |
| 142 | Molecular beam epitaxial growth of BSCCO and Bi-based oxides: self-limiting growth of the Bi element. , 1998, , . | | 0 |
| 143 | Fabrication and electrical properties of ferroelectric-gate FETS with epitaxial gate structures. Electronics and Communications in Japan, 2004, 87, 24-33. | 0.2 | 0 |
| 144 | Impact of Minority Carrier Response on Characterization of Ge MIS Interface Traps. ECS Transactions, 2009, 19, 117-128. | 0.5 | 0 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 145 | Inversion Layer Mobility in High-k Dielectric MOSFETs - Intrinsic Mobility Degradation by Electric Dipoles at High-k/SiO ₂ Interface. ECS Transactions, 2009, 16, 67-75. | 0.5 | 0 |
| 146 | Influence of fin height on poly-Si/PVD-TiN stacked gate FinFET performance. , 2011, , . | | 0 |
| 147 | Two-step annealing effects on ultrathin EOT higher-k (k = 40) ALD-HfO<inf>2</inf> gate stacks. , 2012, , . | | 0 |
| 148 | Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05. | 1.5 | 0 |
| 149 | Extremely Scaled Equivalent Oxide Thickness of High-k (k=40) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Ti Cap Anneal. Hyomen Kagaku, 2012, 33, 610-615. | 0.0 | 0 |
| 150 | Analysis of V _{th} flexibility in ultrathin-BOX SOI FinFETs. , 2013, , . | | 0 |
| 151 | (Invited) Extremely Short Channel Si-MOSFETs Prepared on SOI Substrates Using Anisotropic Wet Etching. ECS Transactions, 2013, 58, 273-280. | 0.5 | 0 |
| 152 | Suppressed variability of current-onset voltage of FinFETs by improvement of work function uniformity of metal gates. , 2013, , . | | 0 |
| 153 | Experimental study of charge trapping type FinFET flash memory. , 2014, , . | | 0 |
| 154 | Modeling of parallel electric field tunnel FETs. , 2015, , . | | 0 |
| 155 | Highly V _t tunable and low variability triangular fin-channel MOSFETs on SOTB. Microelectronic Engineering, 2015, 147, 290-293. | 2.4 | 0 |
| 156 | Evolution of nanoscale silicon CMOS technology for ultra low power application. , 2015, , . | | 0 |
| 157 | Structural and electrical characterization of epitaxial Ge thin films on Si(001) formed by sputtering. Japanese Journal of Applied Physics, 2017, 56, 04CB01. | 1.5 | 0 |
| 158 | Estimation of charge effects of ultrafine channel utilizing junctionless transistor with nanodot-type floating gate. Japanese Journal of Applied Physics, 2017, 56, 03BB05. | 1.5 | 0 |
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